CLAIMS

1. ~~(amended)~~ A tungsten sintered compact sputtering target, wherein, based on a grain size distribution measurement of a W powder used during sintering, sintering is performed using a W powder in which a grain size ratio of tungsten grains of 10 μm or less is 30% or more and less than 70%, and a molybdenum content is 3 ppm or less.

2. The tungsten sintered compact sputtering target according to claim 1, wherein a molybdenum strength detected with a secondary ion mass spectrometer (D-SIMS) is equal to or less than 1/10000 of tungsten strength.

3. The tungsten sintered compact sputtering target according to claim 1, wherein a molybdenum strength detected with a secondary ion mass spectrometer (D-SIMS) is equal to or less than 1/100000 of tungsten strength.

4. The tungsten sintered compact sputtering target according to claim 1, wherein a molybdenum strength detected with a secondary ion mass spectrometer (D-SIMS) is equal to or less than 1/1000000 of tungsten strength.

5. The tungsten sintered compact sputtering target according to any one of claims 1 to 4, wherein a film resistance after subjecting a sputtered film to heating treatment (heat treatment) at 850°C for 60 minutes is 95% or less in comparison to a sputtered film that was not subject to heat treatment (non-heat treated sputtered film).

6. The tungsten sintered compact sputtering target according to any one of claims 1 to 5, wherein a molybdenum content in the tungsten target used in sputtering is 3 ppm or less.

~~7. A tungsten thin film deposited using the tungsten sintered compact sputtering target according to any one of claims 1 to 6.~~